
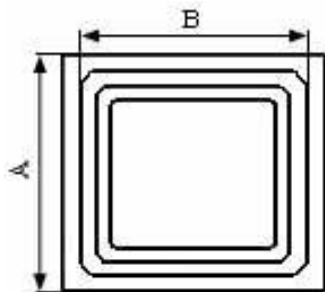
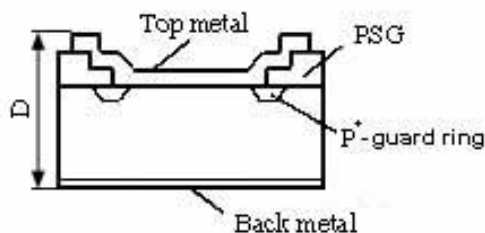


		30A/45V. Die Size-106*158mil. 		
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10mA$	V_{BR}	V	45	50
Average Rectified Forward Current	$I_{F(AV)}$	A	30,0	-
DC Forward Voltage @ 25°C, $I_F=15,0A$ @ 25°C, $I_F=20,0A$ @ 25°C, $I_F=30,0A$	V_F	V	0,49 0,52 0,58	0,47 0,50 0,56
Maximum Reverse Current @ 25°C, $V_R=50V$ @ 25°C, $V_R=45V$ @ 125°C, $V_R=45V$	I_R	mA	- 0,300 150,0	0,300 0,200 130,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	300	-
Peak Repetitive Reverse Surge Current @2,0μs, f=1kHz., $T_J<150°C$.	I_{RRM}	A	5,0	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/μS	10.000	
Operating Junction Temperature	T_J	°C	150	



DIM	ITEM	μm
A_x A_y	Wafer Form Die Size	2700 4000
B_x B_y	Top Metal Size	2560 3860
D	Thickness	300max.
Scribe line Width		80



Top metal:

- a) Al – for Wire Bonding;
 - b) Al-Ni-Ag – for Soldering.
- Backside metal: **Ti-Ni-Ag**.